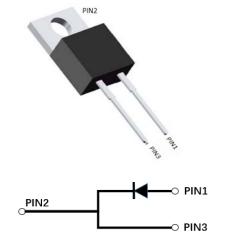


YJD112002PG1

RoHS COMPLIANT

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	4.6A
Qc	13.7nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (1 _c =25℃	Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112002PG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C			9.6
Continuous forward current @ T _c =135°C	I _F	А	4.6
Continuous forward current @ T _c =165°C			2
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	29
Power Dissipation@ T _c =25°C	Ртот	W	62
Power Dissipation@ T _c =110°C	ГТОТ		27
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	4.2
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



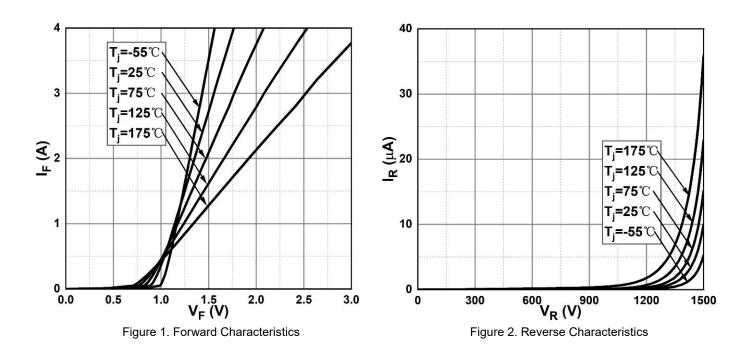
Electrical Characteristics

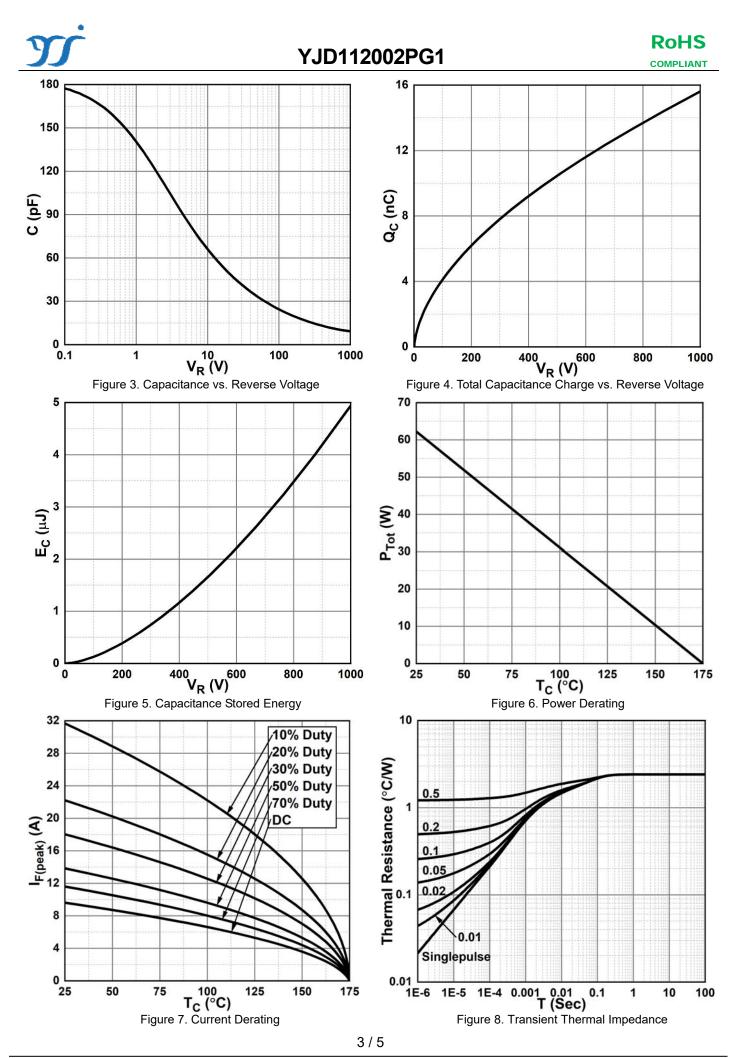
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.	
Forward voltage drap	V _F V	V _F V	I _F =2A, T _j =25°C	1.36	1.55	
Forward voltage drop			I _F =2A, T _j =175°C	2.0	-	
Poverse leakage ourrent				V _R =1200V, T _j =25°C	0.5	10
Reverse leakage current	I _R	μA	V _R =1200V, T _j =175°C	10	-	
Total capacitive charge	Qc	nC	V_R =800V, T _j =25°C , Q_C = \int_0^{VR} C(V)dV	13.7	-	
	с	pF	V _R =0V, f=1MHZ	183	-	
Total capacitance			V _R =400V, f=1MHZ	13	-	
		V _R =800V, f=1MHZ	10	-		
Capacitance Stored Energy	Ec	μJ	V _R =800V	3.5	-	

Thermal Characteristics $(T_a=25^{\circ}C \text{ Unless otherwise specified})$

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C W	2.41

■Typical Characteristics

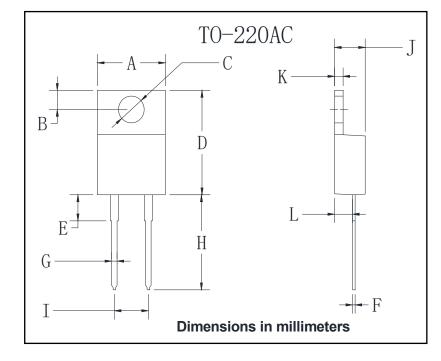




Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions



TO-220AC				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
К	1.14	1.4		
L	2.37	2.79		



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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